

# NCE N-Channel Super Trench Power MOSFET

#### Description

The NCEP01T11 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **General Features**

- V<sub>DS</sub> =100V,I<sub>D</sub> =108A
  R<sub>DS(ON)</sub>=6.2mΩ (typical) @ V<sub>GS</sub>=10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

## Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

#### 100% UIS TESTED!

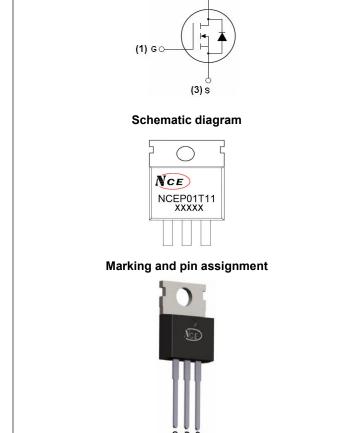
100% ΔVds TESTED!

#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP01T11	NCEP01T11	TO-220-3L	-	-	-

#### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	VDS	100	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	ID	108	A	
Drain Current-Continuous(Tc=100 ℃)	I <sub>D</sub> (100℃)	78	A	
Pulsed Drain Current	І <sub>дм</sub>	432	A	
Maximum Power Dissipation	PD	160	W	
Derating factor		1.1	W/℃	
Single pulse avalanche energy (Note 1)	E <sub>AS</sub>	676	mJ	
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C	



TO-220-3L top view

(2) D



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#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case Rejc	0.94 °C/W
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#### Electrical Characteristics (Tc=25<sup>°</sup>Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	ı					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
On Characteristics	· ·					
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	2.5	-	4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =10V, I <sub>D</sub> =50A	-	6.2	7.0	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =50A	40	-	-	S
Dynamic Characteristics	· ·					
Input Capacitance	Clss		-	4300	-	PF
Output Capacitance	Coss	$V_{DS}$ =50V, $V_{GS}$ =0V,	-	790	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	47	-	PF
Switching Characteristics (Note 2)			•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	13	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =50V,I <sub>D</sub> =50A	-	58	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =4.7 $\Omega$	-	39	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Qg		-	60		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =50V,I <sub>D</sub> =50A,	-	21		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	11		nC
Drain-Source Diode Characteristics	· · ·		· ·			
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =108A	-		1.2	V
Diode Forward Current	ls		-	-	108	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>	-	60		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	140		nC

#### Notes:

1. EAS condition : Tj=25  $^\circ \!\! \mathbb{C}$  ,V\_DD=50V,V\_G=10V,L=0.5mH,Rg=25\Omega

2. Guaranteed by design, not subject to production

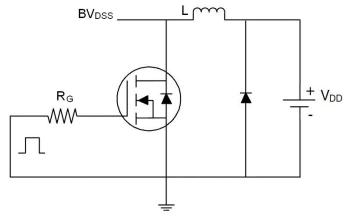
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.



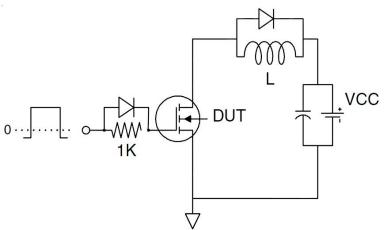
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# Test Circuit

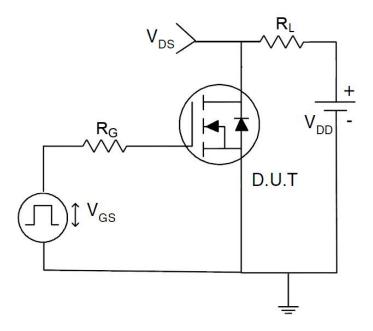
1) E<sub>AS</sub> test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





125

50

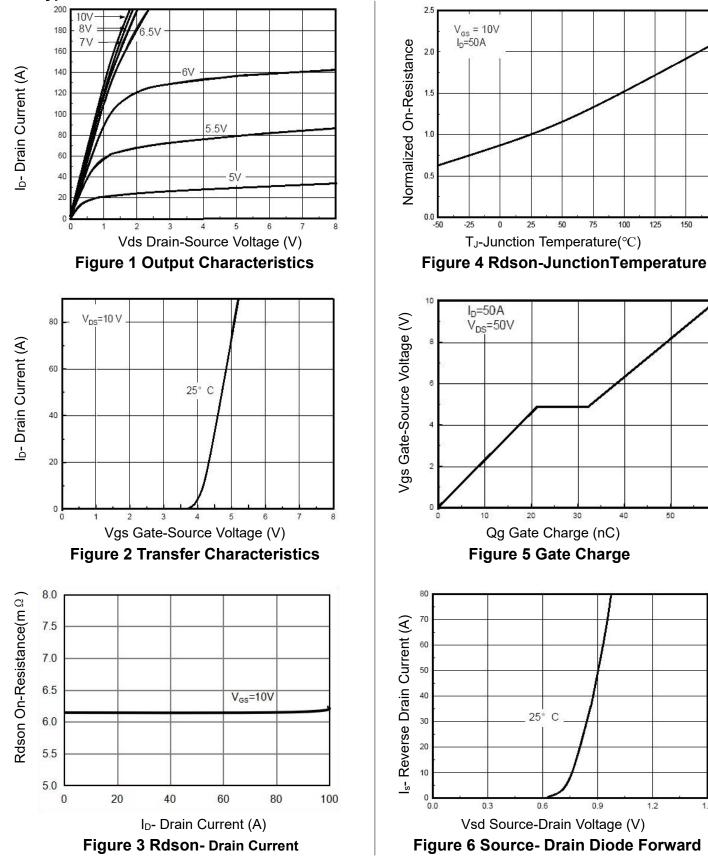
1.2

60

150

175

## **Typical Electrical and Thermal Characteristics**



1.5



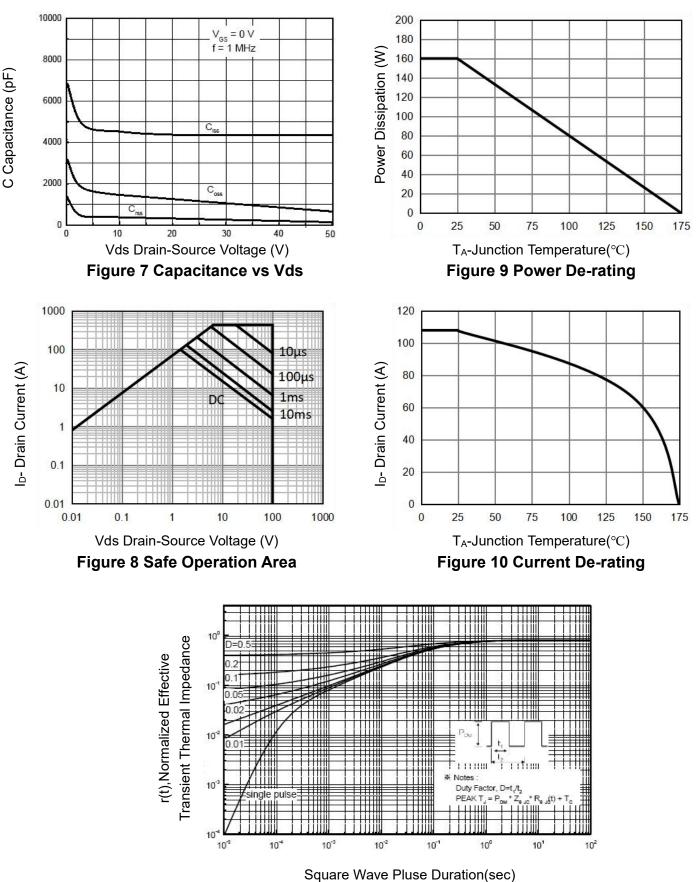
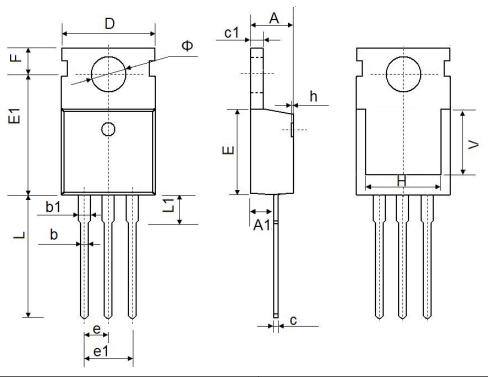


Figure 11 Normalized Maximum Transient Thermal Impedance



## TO-220-3L Package Information



Current of	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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